

Kwang-Sik Jeong

List of Publications by Year in descending order

Source: <https://exaly.com/author-pdf/3738442/publications.pdf>

Version: 2024-02-01

47
papers

671
citations

516710

16
h-index

642732

23
g-index

47
all docs

47
docs citations

47
times ranked

1006
citing authors

#	ARTICLE	IF	CITATIONS
1	Switching to Hidden Metallic Crystal Phase in Phase-Change Materials by Photoenhanced Metavalent Bonding. ACS Nano, 2022, , .	14.6	2
2	Ferroelasticâ€“Ferroelectric Multiferroicity in van der Waals Rhenium Dichalcogenides. Advanced Materials, 2022, 34, e2108777.	21.0	10
3	Interaction- and defect-free van der Waals contacts between metals and two-dimensional semiconductors. Nature Electronics, 2022, 5, 241-247.	26.0	84
4	Controlling resistive switching behavior in the solution processed SiO ₂ -x device by the insertion of TiO ₂ nanoparticles. Scientific Reports, 2022, 12, 8405.	3.3	3
5	Optical characteristics of type-II hexagonal-shaped GaSb quantum dots on GaAs synthesized using nanowire self-growth mechanism from Ga metal droplet. Scientific Reports, 2021, 11, 7699.	3.3	3
6	Enhanced Spin-to-Charge Conversion Efficiency in Ultrathin Bi ₂ Se ₃ Observed by Spintronic Terahertz Spectroscopy. ACS Applied Materials & Interfaces, 2021, 13, 23153-23160.	8.0	11
7	Modulation of optoelectronic properties of the Bi ₂ Te ₃ nanowire by controlling the formation of selective surface oxidation. Applied Surface Science, 2021, 548, 149069.	6.1	10
8	Enhancement of photoresponse in Bi ₂ Se ₃ /graphene heterostructures by effective electronâ€“hole separation through internal band bending. Applied Surface Science, 2021, 554, 149623.	6.1	8
9	Quantitative analysis of defect states in amorphous InGaZnO thin-film transistors using photoinduced current transient spectroscopy. Journal of Applied Physics, 2021, 130, .	2.5	6
10	Ferroelectric switching in GeTe through rotation of lone-pair electrons by Electric field-driven phase transition. Applied Materials Today, 2021, 24, 101122.	4.3	7
11	Ultrathin platinum diselenide synthesis controlling initial growth kinetics: Interfacial reaction depending on thickness and substrate. Applied Surface Science, 2021, 564, 150300.	6.1	7
12	Phase Change <i>via</i> Intermediary Metastable Local Structure of Ge Atoms in Ge ₂ Sb ₂ Te ₅ Nanowires during Electrical Switching. ACS Applied Electronic Materials, 2020, 2, 2418-2428.	4.3	1
13	Enhanced Photoinduced Carrier Generation Efficiency through Surface Band Bending in Topological Insulator Bi ₂ Se ₃ Thin Films by the Oxidized Layer. ACS Applied Materials & Interfaces, 2020, 12, 26649-26658.	8.0	12
14	Topological Phase Control of Surface States in Bi ₂ Se ₃ via Spinâ€“Orbit Coupling Modulation through Interface Engineering between HfO ₂ â€“X. ACS Applied Materials & Interfaces, 2020, 12, 12215-12226.	8.0	4
15	Quantification of point and line defects in Si _{0.6} Ge _{0.4} alloys with thickness variation via optical pump-THz probe measurement. Applied Surface Science, 2020, 513, 145815.	6.1	1
16	Ultrafast Photoâ€“Response by Surface Stateâ€“Mediated Optical Transitions in Topological Insulator Bi ₂ Te ₃ Nanowire. Advanced Optical Materials, 2019, 7, 1900621.	7.3	11
17	Trap-assisted high responsivity of a phototransistor using bi-layer MoSe ₂ grown by molecular beam epitaxy. Applied Surface Science, 2019, 494, 37-45.	6.1	9
18	Closing the Surface Bandgap in Thin Bi ₂ Se ₃ /Graphene Heterostructures. ACS Nano, 2019, 13, 3931-3939.	14.6	20

#	ARTICLE	IF	CITATIONS
19	P _n -N Junction Diode Using Plasma Boron-Doped Black Phosphorus for High-Performance Photovoltaic Devices. ACS Nano, 2019, 13, 1683-1693.	14.6	23
20	Effects of thermal and electrical stress on defect generation in InAs metal-oxide-semiconductor capacitor. Applied Surface Science, 2019, 467-468, 1161-1169.	6.1	8
21	Improving Electrical Properties by Effective Sulfur Passivation via Modifying the Surface State of Substrate in HfO ₂ /InP Systems. Journal of Physical Chemistry C, 2018, 122, 7226-7235.	3.1	13
22	Effect of substrate on photo-induced persistent photoconductivity in InAs nanowires. Applied Surface Science, 2018, 458, 964-971.	6.1	6
23	Disorder-induced decoupled surface transport channels in thin films of doped topological insulators. Physical Review B, 2018, 98, .	3.2	9
24	Ultrafast photocarrier dynamics related to defect states of Si _{1-x} Ge _x nanowires measured by optical pump-THz probe spectroscopy. Nanoscale, 2017, 9, 8015-8023.	5.6	13
25	Modulation of phase change characteristics in Ag-incorporated Ge ₂ Sb ₂ Te ₅ owing to changes in structural distortion and bond strength. Journal of Materials Chemistry C, 2017, 5, 3973-3982.	5.5	20
26	Oxidation Mechanism of Si _{1-x} Ge _x Nanowires with Au Catalyst Tip as a Function of Ge Content. ACS Applied Materials & Interfaces, 2017, 9, 37411-37418.	8.0	0
27	Electrical properties and thermal stability in stack structure of HfO ₂ /Al ₂ O ₃ /InSb by atomic layer deposition. Scientific Reports, 2017, 7, 11337.	3.3	17
28	Characterization of Rotational Stacking Layers in Large-Area MoSe ₂ Film Grown by Molecular Beam Epitaxy and Interaction with Photon. ACS Applied Materials & Interfaces, 2017, 9, 30786-30796.	8.0	16
29	Effects of resonant bonding and structural distortion on the phase change properties of Sn ₂ Sb ₂ Se ₅ . Journal of Materials Chemistry C, 2017, 5, 7820-7829.	5.5	7
30	Evolution of crystal structures in GeTe during phase transition. Scientific Reports, 2017, 7, 955.	3.3	32
31	Terahertz spectroscopy of topological insulator Sb ₂ Se ₃ and its ultrafast nonequilibrium carrier dynamics. , 2016, , .		0
32	Controlling the defects and transition layer in SiO ₂ films grown on 4H-SiC via direct plasma-assisted oxidation. Scientific Reports, 2016, 6, 34945.	3.3	29
33	Thermal and Electrical Conduction of Single-crystal Bi ₂ Te ₃ Nanostructures grown using a one step process. Scientific Reports, 2016, 6, 19132.	3.3	45
34	Tuning the Fermi level with topological phase transition by internal strain in a topological insulator Bi ₂ Se ₃ thin film. Nanoscale, 2016, 8, 741-751.	5.6	23
35	Structural and Electrical Properties of EOT HfO ₂ (<1 nm) Grown on InAs by Atomic Layer Deposition and Its Thermal Stability. ACS Applied Materials & Interfaces, 2016, 8, 7489-7498.	8.0	18
36	Filament Geometry Induced Bipolar, Complementary and Unipolar Resistive Switching under the Same Set Current Compliance in Pt/SiO _x /TiN. Scientific Reports, 2015, 5, 15374.	3.3	18

#	ARTICLE	IF	CITATIONS
37	Phase-change-induced martensitic deformation and slip system in GeSbTe. RSC Advances, 2015, 5, 35792-35800.	3.6	3
38	Reversible Fermi Level Tuning of a Sb ₂ Te ₃ Topological Insulator by Structural Deformation. Nano Letters, 2015, 15, 3820-3826.	9.1	31
39	Effects of spontaneous nitrogen incorporation by a 4H-SiC(0001) surface caused by plasma nitridation. Journal of Materials Chemistry C, 2015, 3, 5078-5088.	5.5	7
40	Electric field effect dominated bipolar resistive switching through interface control in a Pt/TiO ₂ /TiN structure. RSC Advances, 2015, 5, 221-230.	3.6	18
41	Effect of the Thermal Conductivity on Resistive Switching in GeTe and Ge ₂ Sb ₂ Te ₅ Nanowires. ACS Applied Materials & Interfaces, 2015, 7, 21819-21827.	8.0	25
42	Ultrafast phase change and long durability of BN-incorporated GeSbTe. Journal of Materials Chemistry C, 2015, 3, 1707-1715.	5.5	21
43	Effects of Nitrogen Incorporation in HfO ₂ Grown on InP by Atomic Layer Deposition: An Evolution in Structural, Chemical, and Electrical Characteristics. ACS Applied Materials & Interfaces, 2014, 6, 3896-3906.	8.0	15
44	Structural deformation and void formation driven by phase transformation in the Ge ₂ Sb ₂ Te ₅ film. Journal of Materials Chemistry C, 2014, 2, 2001.	5.5	5
45	The effect of structural and chemical bonding changes on the optical properties of Si/Si _{1-x} C _x core/shell nanowires. Journal of Materials Chemistry C, 2013, 1, 5207.	5.5	3
46	Structural Evolution and the Control of Defects in Atomic Layer Deposited HfO ₂ /Al ₂ O ₃ Stacked Films on GaAs. ACS Applied Materials & Interfaces, 2013, 5, 1982-1989.	8.0	34
47	Induction of the surface plasmon resonance from C-incorporated Au catalyst in Si _{1-x} C _x nanowires. Journal of Materials Chemistry, 2012, 22, 19744.	6.7	3